SN74LVC2G66

SN74LVC2G66 Dual Bilateral Analog Switch

1 Features

- Available in the Texas Instruments NanoFree[™] Package
- 1.65-V to 5.5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 0.8 ns at 3.3 V
- High On-Off Output Voltage Ratio
- High Degree of Linearity
- High Speed, Typically 0.5 ns (V_{CC} = 3 V, C_L = 50 pF)
- Rail-to-Rail Input/Output
- Low ON-State Resistance, Typically ≉6 Ω (V_{CC} = 4.5 V)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

2 Applications

- Wireless Devices
- Audio and Video Signal Routing
- Portable Computing
- Wearable Devices
- Signal Gating, Chopping, Modulation or Demodulation (Modem)
- Signal Multiplexing for Analog-to-Digital and Digital-to-Analog Conversion Systems

3 Description

This dual bilateral analog switch is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G66 device can handle both analog and digital signals. The SN74LVC2G66 device permits signals with amplitudes of up to 5.5 V (peak) to be transmitted in either direction.

NanoFree package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Each switch section has its own enable-input control (C). A high-level voltage applied to C turns on the associated switch section.

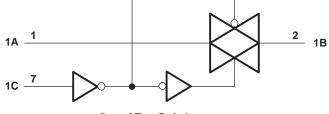
Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
SN74LVC2G66DCT	SSOP (8)	2.95 mm × 2.80 mm		
SN74LVC2G66DCU	VSSOP (8)	2.30 mm × 2.00 mm		
SN74LVC2G66YZP	DSBGA (8)	1.91 mm × 0.91 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram, Each Switch (Positive Logic)



One of Two Switches

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision M (May 2018) to Revision N	Page
Changed the YZP pin configuration	
Changes from Revision L (September 2015) to Revision M	Page
Updated pinout image and the Pin Function table	

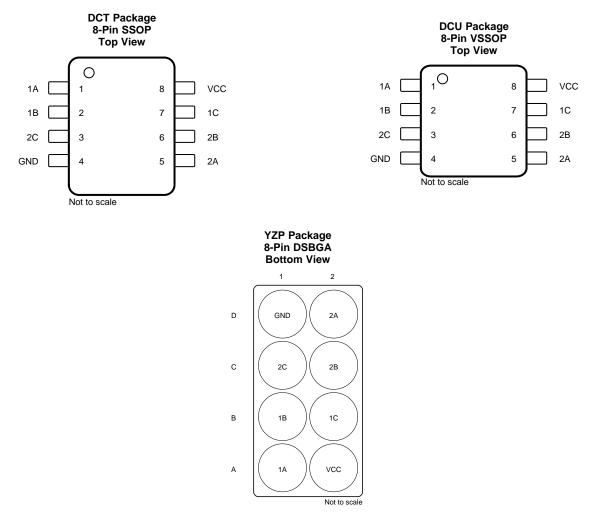
•	Changed pin 3 Name From: 1C To: 2C	3
•	Changed the Thermal Information table for the DCT package	5

Changes from Revision K (January 2014) to Revision L

•	Added Applications section, Device Information table, Pin Configuration and Functions section, ESD Ratings table, Typical Characteristics section, Feature Description section, Device Functional Modes, Application and
	Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation
	Support section, and Mechanical, Packaging, and Orderable Information section
•	Added Thermal Information table

Changes from Revision J (December 2011) to Revision K Page • Updated document to new TI data sheet format--no specification changes. 1 • Removed Ordering Information table. 1

5 Pin Configuration and Functions



See mecahnical drawings for dimensions.

Pin Functions

PIN				
NAME	DCT DCU	YZP	I/O	DESCRIPTION
1A	1	A1	I/O	Bidirectional signal to be switched
1B	2	B1	I/O	Bidirectional signal to be switched
2C	3	C1	I	Controls the switch (L = OFF, H = ON)
2A	5	D2	I/O	Bidirectional signal to be switched
2B	6	C2	I/O	Bidirectional signal to be switched
1C	7	B2	I	Controls the switch (L = OFF, H = ON)
GND	4	D1	_	Ground pin
V _{CC}	8	A2	—	Power pin

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage ⁽²⁾		-0.5	6.5	V
VI	Input voltage ⁽²⁾⁽³⁾		-0.5	6.5	V
Vo	Switch I/O voltage ⁽²⁾⁽³⁾⁽⁴⁾		-0.5	V _{CC} + 0.5	V
I _{IK}	Control input clamp current	V _I < 0		-50	mA
I _{I/OK}	I/O port diode current	$V_{I/O} < 0 \text{ or } V_{I/O} > V_{CC}$		-50	mA
I _T	On-state switch current	$V_{I/O} = 0$ to V_{CC}		±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T _{stg}	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to ground, unless otherwise specified.

(3) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

(4) This value is limited to 5.5 V maximum.

6.2 ESD Ratings

			VALUE	UNIT
	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	
V _(ESD)	discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

See (1).

			MIN	MAX	UNIT	
V _{CC}	Supply voltage		1.65	5.5	V	
V _{I/O}	I/O port voltage		0	V _{CC}	V	
		V_{CC} = 1.65 V to 1.95 V	V _{CC} × 0.65			
V _{IH}	High-level input voltage, control input	V_{CC} = 2.3 V to 2.7 V	$V_{CC} \times 0.7$		V	
		$V_{CC} = 3 V \text{ to } 3.6 V$	$V_{CC} \times 0.7$		v	
		V_{CC} = 4.5 V to 5.5 V	$V_{CC} \times 0.7$			
		V_{CC} = 1.65 V to 1.95 V		$V_{CC} \times 0.35$	V	
V	Low-level input voltage, control input	V_{CC} = 2.3 V to 2.7 V		$V_{CC} \times 0.3$		
V _{IL}		$V_{CC} = 3 V \text{ to } 3.6 V$		$V_{CC} \times 0.3$	V	
		V_{CC} = 4.5 V to 5.5 V		$V_{CC} \times 0.3$		
VI	Control input voltage		0	5.5	V	
		V_{CC} = 1.65 V to 1.95 V		20		
A #/ A > /		V_{CC} = 2.3 V to 2.7 V		20	20/1	
$\Delta t / \Delta v$	Input transition rise or fall time	$V_{CC} = 3 V \text{ to } 3.6 V$		10	ns/V	
	V _{CC} = 4.5 V to 5.5 V			10		
T _A	Operating free-air temperature		-40	85	°C	

 All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

6.4 Thermal Information

			SN74LVC2G66			
	THERMAL METRIC ⁽¹⁾	DCT (SSOP)	DCU (VSSOP)	YZP (DSBGA)	UNIT	
		8 PINS	8 PINS	8 PINS		
R_{\thetaJA}	Junction-to-ambient thermal resistance	186.1	204.4	102	°C/W	
R _{0JC(top)}	Junction-to-case (top) thermal resistance	116.5	77	_	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	98.6	83.2	_	°C/W	
ΨJT	Junction-to-top characterization parameter	42.2	7.1	—	°C/W	
ΨЈВ	Junction-to-board characterization parameter	97.6	82.7	_	°C/W	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	n/a	_	°C/W	

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITI	ONS	V _{cc}	MIN TYP ⁽¹⁾	MAX	UNIT	
			$I_{S} = 4 \text{ mA}$	1.65 V	12.5	30		
-	ON-state switch resistance	$V_I = V_{CC}$ or GND,	$I_S = 8 \text{ mA}$	2.3 V	9	20	Ω	
r _{on}	On-state switch resistance	$V_{C} = V_{IH}$ (see Figure 3 and Figure 1)	$I_{S} = 24 \text{ mA}$	3 V	7.5	15	Ω	
			I _S = 32 mA	4.5 V	6	10		
			$I_S = 4 \text{ mA}$	1.65 V	85	120 ⁽¹⁾		
-	Peak ON-state resistance	$V_{I} = V_{CC}$ to GND,	$I_{S} = 8 \text{ mA}$	2.3 V	22	30 ⁽¹⁾	Ω	
r _{on(p)}	ion(p) i car On-State resistance	$V_{C} = V_{IH}$ (see Figure 3 and Figure 1)	I _S = 24 mA	3 V	12	20	12	
			I _S = 32 mA	4.5 V	7.5	15		
			$I_{S} = 4 \text{ mA}$	1.65 V		7		
A =	Difference of ON-state resistance between switches		I _S = 8 mA	2.3 V		5	Ω	
Δr_{on}			I _S = 24 mA	3 V		3		
			I _S = 32 mA	4.5 V		2		
		$V_I = V_{CC}$ and $V_O = GND$ or				±1		
I _{S(off)}	OFF-state switch leakage current	$V_I = GND \text{ and } V_O = V_{CC},$ $V_C = V_{IL} \text{ (see Figure 4)}$		5.5 V		±0.1 ⁽¹⁾	μA	
	ON-state switch leakage current	$V_{I} = V_{CC}$ or GND, $V_{C} = V_{IH}$, V_{C}) = Open	5.5 V		±1	μA	
I _{S(on)}	ON-State Switch leakage current	(see Figure 5)		5.5 V	±0.1 ⁽¹⁾		μΑ	
	Control input current	V = V or CND		5.5 V		±1	μA	
I	Control input current	$V_{C} = V_{CC}$ or GND		5.5 V		±0.1 ⁽¹⁾		
	Supply aurrent			5 5 V		10	۵	
I _{CC}	Supply current	$V_{C} = V_{CC}$ or GND		5.5 V		1 ⁽¹⁾	μΑ	
ΔI_{CC}	Supply-current change	$V_{\rm C} = V_{\rm CC} - 0.6 \ V$		5.5 V		500	μA	
C _{ic}	Control input capacitance			5 V	3.5		pF	
C _{io(off)}	Switch input / output capacitance			5 V	6		pF	
C _{io(on)}	Switch input / output capacitance			5 V	14		pF	

(1) $T_A = 25^{\circ}C$

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6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1	1.8 V 5 V	V _{CC} = 2 ± 0.2		V _{CC} = 2 ± 0.3		V _{CC} = ± 0.5		UNIT
	(INPUT)	(001F01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd} ⁽¹⁾	A or B	B or A		2		1.2		0.8		0.6	ns
t _{en} ⁽²⁾	С	A or B	2.3	10	1.6	5.6	1.5	4.4	1.3	3.9	ns
t _{dis} ⁽³⁾	С	A or B	2.5	10.5	1.2	6.9	2	7.2	1.1	6.3	ns

(1) t_{PLH} and t_{PHL} are the same as t_{pd}. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

(2) t_{PZL} and t_{PZH} are the same as t_{en} .

(3) t_{PLZ} and t_{PHZ} are the same as t_{dis} .

6.7 Analog Switch Characteristics

 $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{cc}	ТҮР	UNIT
				1.65 V	35	
			$C_{L} = 50 \text{ pF}, R_{L} = 600 \Omega,$	2.3 V	120	
			f _{in} = sine wave (see Figure 6)	3 V	175	
Frequency response	A or B	B or A		4.5 V	195	MHz
(switch on)	AOLP	BUIA		1.65 V	>300	IVIEZ
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	>300	
			f _{in} = sine wave (see Figure 6)	3 V	>300	
				4.5 V	>300	
				1.65 V	-58	
Crosstalk ⁽¹⁾ (between switches)		B or A	$C_{L} = 50 \text{ pF}, R_{L} = 600 \Omega,$	2.3 V	-58	dB
			f _{in} = 1 MHz (sine wave) (see Figure 7)	3 V	-58	
	A or B			4.5 V	-58	
	A OF B			1.65 V	-42	
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	-42	
			f _{in} = 1 MHz (sine wave) (see Figure 7)	3 V	-42	
				4.5 V	-42	
				1.65 V	35	mV
Crosstalk		A	$C_{L} = 50 \text{ pF}, R_{L} = 600 \Omega,$	2.3 V	50	
(control input to signal output)	С	A or B	f _{in} = 1 MHz (square wave) (see Figure 8)	3 V	70	
			()	4.5 V	100	
				1.65 V	-58	
			$C_{L} = 50 \text{ pF}, R_{L} = 600 \Omega,$	2.3 V	-58	
			f _{in} = 1 MHz (sine wave) (see Figure 9)	3 V	-58	
Feedthrough attenuation	A			4.5 V	-58	JD
(switch off)	A or B	B or A		1.65 V	-42	dB
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	-42	
			f _{in} = 1 MHz (sine wave) (see Figure 9)	3 V	-42	
				4.5 V	-42	

Analog Switch Characteristics (continued)

$T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{cc}	ТҮР	UNIT
				1.65 V	0.1%	
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$ $f_{in} = 1 \text{ kHz}$ (sine wave)	2.3 V	0.025%	
			(see Figure 10) 3 V 4.5 1.65	3 V	0.015%	
Sine-wave distortion	A or B	B or A		4.5 V	0.01%	
Sine-wave distortion	AUB	BUIA		1.65 V	0.15%	
				2.3 V	0.025%	
			$I_{in} = 10$ km² (sine wave) (see Figure 10)	3 V	0.015%	
				4.5 V	0.01%	

6.8 Operating Characteristics

 $T_A = 25^{\circ}C$

PARAMETER		TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	$V_{CC} = 5 V$	UNIT
		CONDITIONS	ТҮР	ТҮР	ТҮР	TYP	UNIT
C_{pd}	Power dissipation capacitance	f = 10 MHz	8	9	9.5	11	pF

6.9 Typical Characteristics

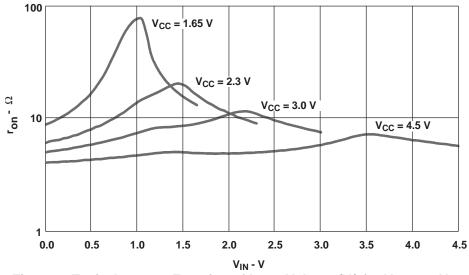
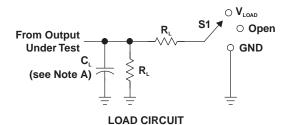


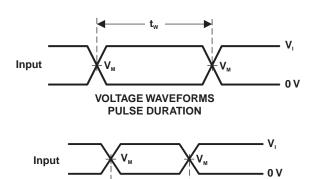
Figure 1. Typical r_{on} as a Function of Input Voltage (V_I) for V_I = 0 to V_{CC}

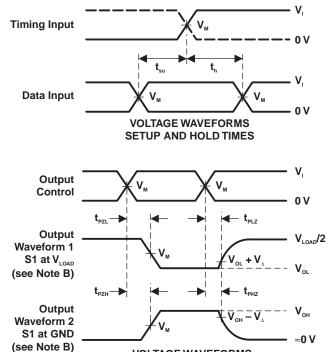
7 Parameter Measurement Information



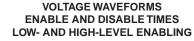
TEST	S1
t _{PLH} /t _{PHL}	Open
t_{PLZ}/t_{PZL}	V_{load}
t _{PHZ} /t _{PZH}	GND

N N	IN	PUTS			_	-		
V _{cc}	V	t,/t,	V _M	VLOAD	C	R	\mathbf{V}_{Δ}	
$1.8V\pm0.15V$	V _{cc}	≤2 ns	V _{cc} /2	$2 \times V_{cc}$	30 pF	1 k Ω	0.15 V	
$\textbf{2.5 V} \pm \textbf{0.2 V}$	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V	
$3.3V\pm0.3V$	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V	
5 V \pm 0.5 V	V_{cc}	≤2.5 ns	V _{cc} /2	$2 \times V_{cc}$	50 pF	500 Ω	0.3 V	





VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS



NOTES: A. C_L includes probe and jig capacitance.

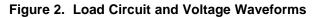
Output

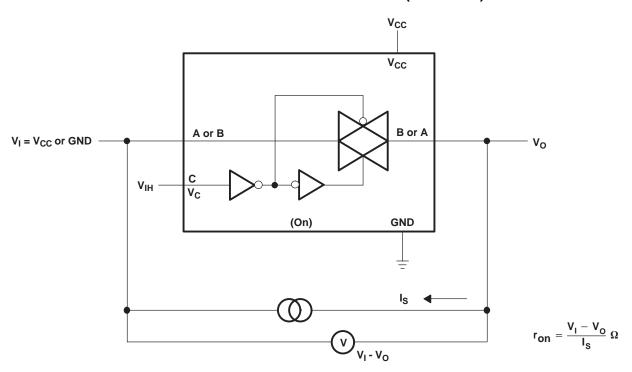
Output

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control. C. All input pulses are supplied by generators have the following characteristics: PRR \leq 10 MHz, Z_o = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.

V_o

- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. $t_{\mbox{\tiny PZL}}$ and $t_{\mbox{\tiny PZH}}$ are the same as $t_{\mbox{\tiny en}}.$
- G. $t_{\mbox{\tiny PLH}}$ and $t_{\mbox{\tiny PHL}}$ are the same as $t_{\mbox{\tiny pd}}^{-}$
- H. All parameters and waveforms are not applicable to all devices.





Parameter Measurement Information (continued)

Figure 3. ON-State Resistance Test Circuit

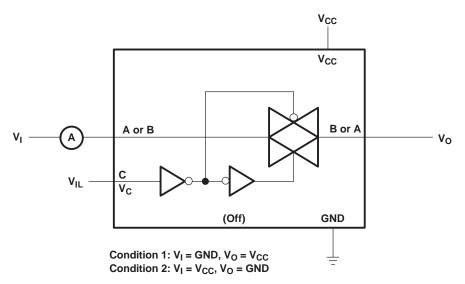
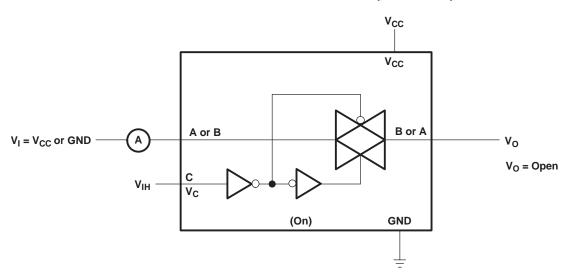


Figure 4. OFF-State Switch Leakage-Current Test Circuit



Parameter Measurement Information (continued)

Figure 5. ON-State Leakage-Current Test Circuit

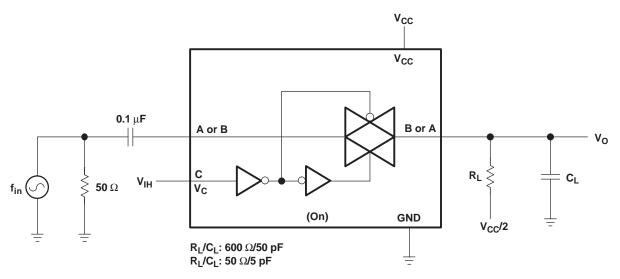
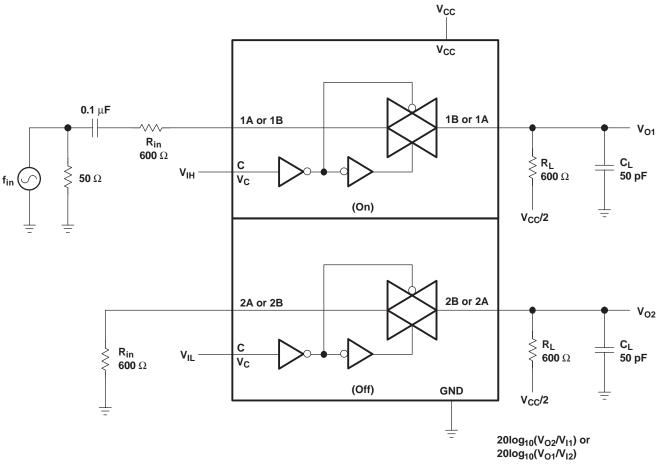
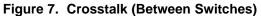


Figure 6. Frequency Response (Switch On)



Parameter Measurement Information (continued)



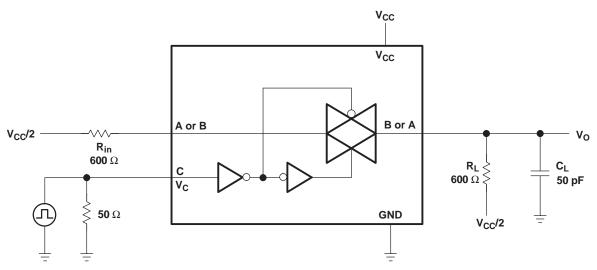
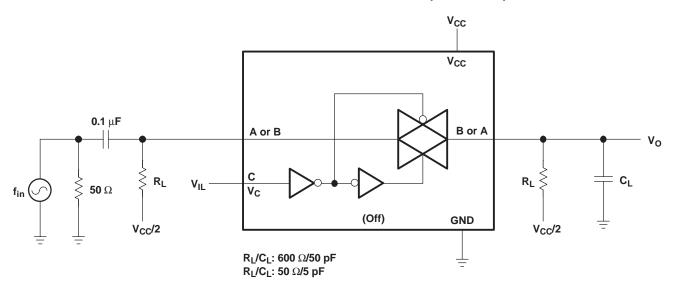


Figure 8. Crosstalk (Control Input, Switch Output)



Parameter Measurement Information (continued)



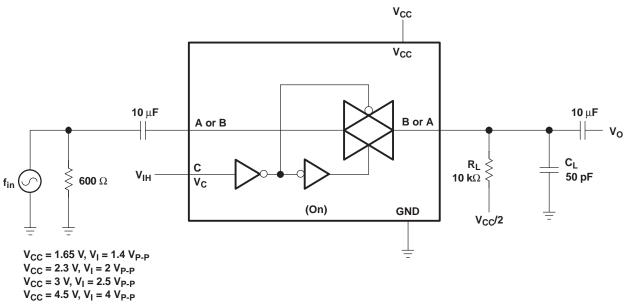


Figure 10. Sine-Wave Distortion

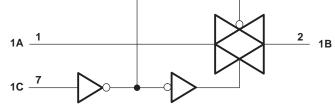
8 Detailed Description

8.1 Overview

This dual bilateral analog switch is designed for 1.65-V to 5.5-V V_{CC} operation. Robust LVC family technology allows this device to accept input voltages without connecting power to V_{CC} .

The SN74LVC2G66 device permits signals with amplitudes of up to 5.5 V (peak) to be transmitted in either direction. A high-level voltage applied to the control pin C enables the respective switch to begin propagating signals across the device. A low-level voltage disables this transmission. Each device incorporates two switches with independent control and operation.

8.2 Functional Block Diagram



One of Two Switches

8.3 Feature Description

Each switch section has its own enable-input control (C). A high-level voltage applied to C turns on the associated switch section. When C is this Signals can pass through A to B or B to A. Low ON-resistance of 6 Ω at 4.5-V V_{CC} is ideal for analog signal conditioning systems. The control signals can accept voltages up to 5.5 V without V_{CC} connected in the system. Combination of lower t_{pd} of 0.8 ns at 3.3 V and low enable and disable time make this part suitable for high-speed signal switching applications.

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74LVC2G66.

Table 1. Function Table

CONTROL INPUT (C)	SWITCH
L	Off
н	On

9 Application and Implementation

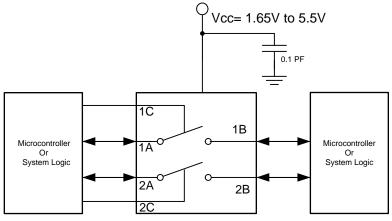
NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC2G66 can be used in any situation where an Dual SPST switch would be used and a solid-state, voltage controlled version is preferred.

9.2 Typical Application



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Figure 11. Typical Application Schematic

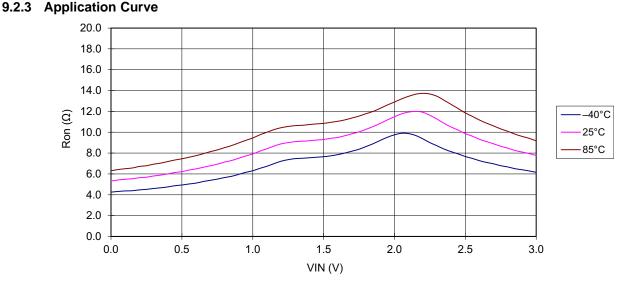
9.2.1 Design Requirements

The SN74LVC2G66 allows on/off control of analog and digital signals with a digital control signal. All input signals should remain between 0 V and V_{CC} for optimal operation.

9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
 - For rise time and fall time specifications, see $\Delta t / \Delta v$ in the Recommended Operating Conditions table.
 - For specified high and low levels, see V_{IH} and V_{IL} in the *Recommended Operating Conditions* table.
 - Inputs and outputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.
- 2. Recommended Output Conditions:
 - Load currents should not exceed ±50 mA.
- 3. Frequency Selection Criterion:
 - Maximum frequency tested is 150 MHz.
 - Added trace resistance or capacitance can reduce maximum frequency capability; use layout practices as directed in *Layout*.

Typical Application (continued)



Pin: A–B, V_{CC} = 3 V, I_S = 24 mA

Figure 12. ron vs VI

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F bypass capacitor is recommended. If there are multiple pins labeled V_{CC}, then a 0.01- μ F or 0.022- μ F capacitor is recommended for each V_{CC} because the VCC pins will be tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD}, a 0.1- μ F bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to loop antenna theory, but different enough to warrant their own discussion. When a PCB trace turns a corner at a 90° angle, a reflection can occur. This is primarily due to the change of width of the trace. At the apex of the turn, the trace width is increased to 1.414 times its width. This upsets the transmission line characteristics, especially the distributed capacitance and self–inductance of the trace — resulting in the reflection.

NOTE Not all PCB traces can be straight, and so they will have to turn corners. Figure 13 shows progressively better techniques of rounding corners. Only the last example maintains constant trace width and minimizes reflections.

11.2 Layout Example

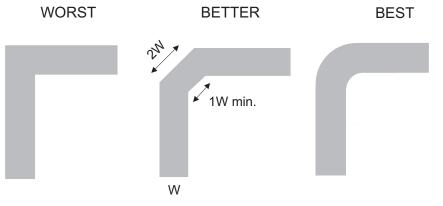


Figure 13. Trace Example

12 Device and Documentation Support

12.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E[™] Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.2 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status	Package Type		Pins	Package		Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN74LVC2G66DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)	Samples
SN74LVC2G66DCTRE4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)	Samples
SN74LVC2G66DCTRG4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)	Samples
SN74LVC2G66DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(66, C66Q, C66R) CZ	Samples
SN74LVC2G66DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R	Samples
SN74LVC2G66DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(C66Q, C66R)	Samples
SN74LVC2G66DCUTE4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R	Samples
SN74LVC2G66DCUTG4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R	Samples
SN74LVC2G66YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(C67, C6N)	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

PACKAGE OPTION ADDENDUM

10-Dec-2020

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LVC2G66 :

Automotive: SN74LVC2G66-Q1

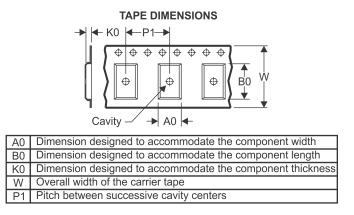
NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

27-May-2021

TAPE AND REEL INFORMATION





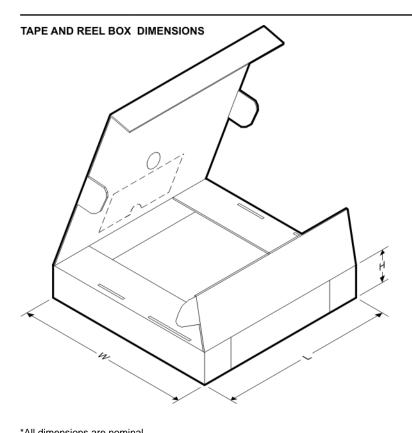
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G66DCTR	SM8	DCT	8	3000	177.8	12.4	3.45	4.4	1.45	4.0	12.0	Q3
SN74LVC2G66DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.25	3.4	1.0	4.0	8.0	Q3
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

PACKAGE MATERIALS INFORMATION

27-May-2021



*All dimensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G66DCTR	SM8	DCT	8	3000	183.0	183.0	20.0
SN74LVC2G66DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G66DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G66DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G66YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

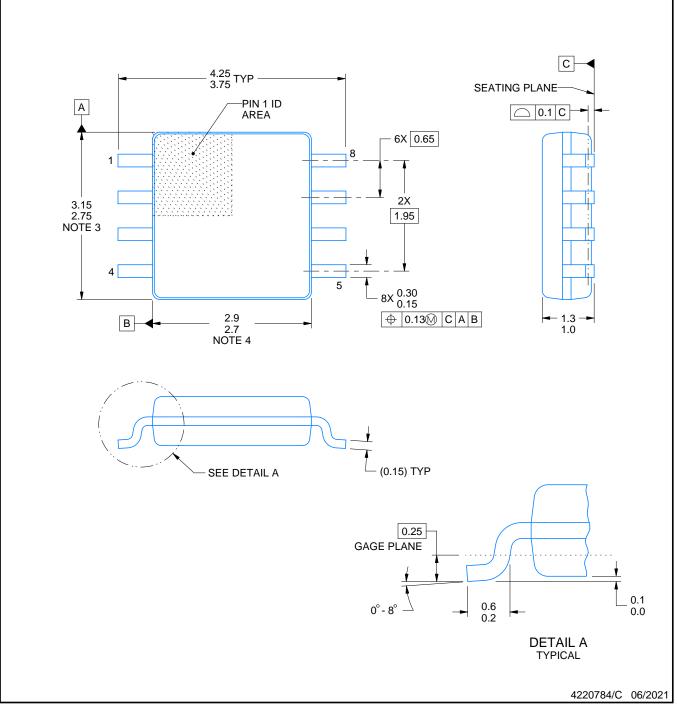
DCT0008A



PACKAGE OUTLINE

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



NOTES:

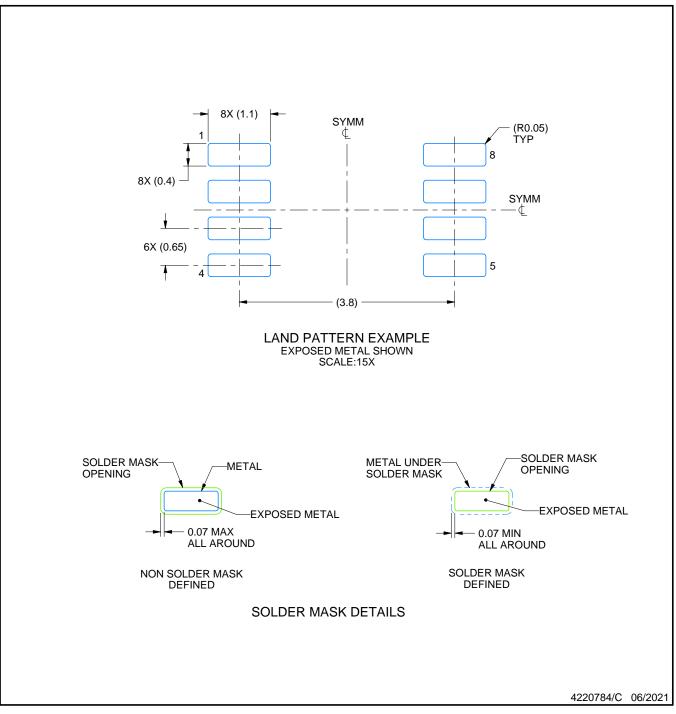
- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.

DCT0008A

EXAMPLE BOARD LAYOUT

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

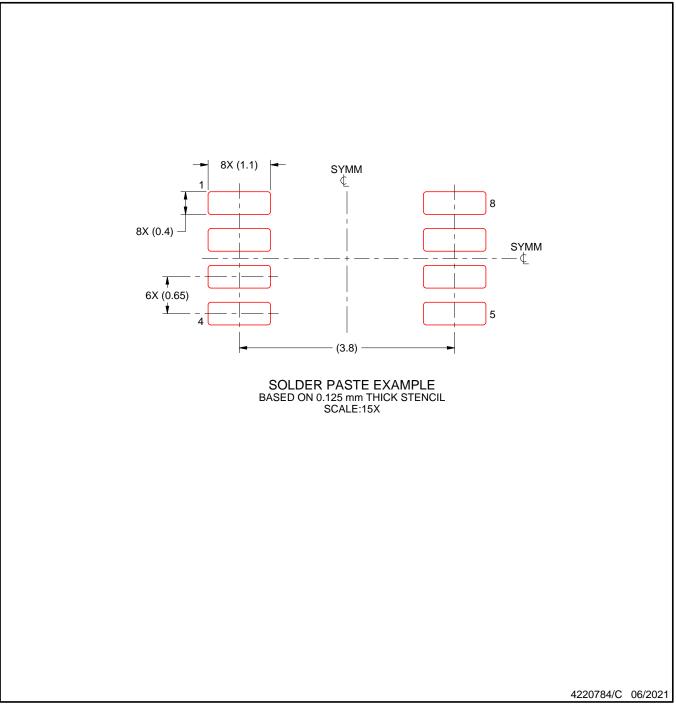
Publication IPC-7351 may have alternate designs.
 Solder mask tolerances between and around signal pads can vary based on board fabrication site.

DCT0008A

EXAMPLE STENCIL DESIGN

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

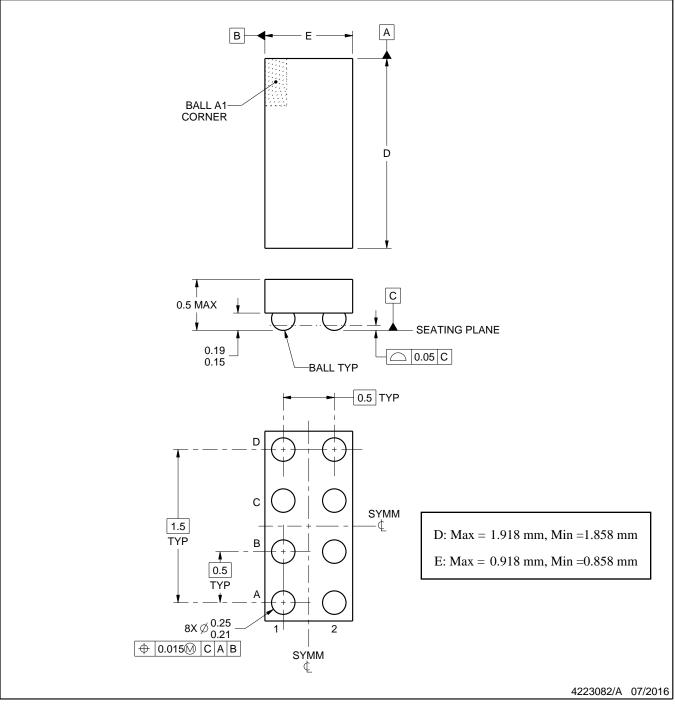
YZP0008



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

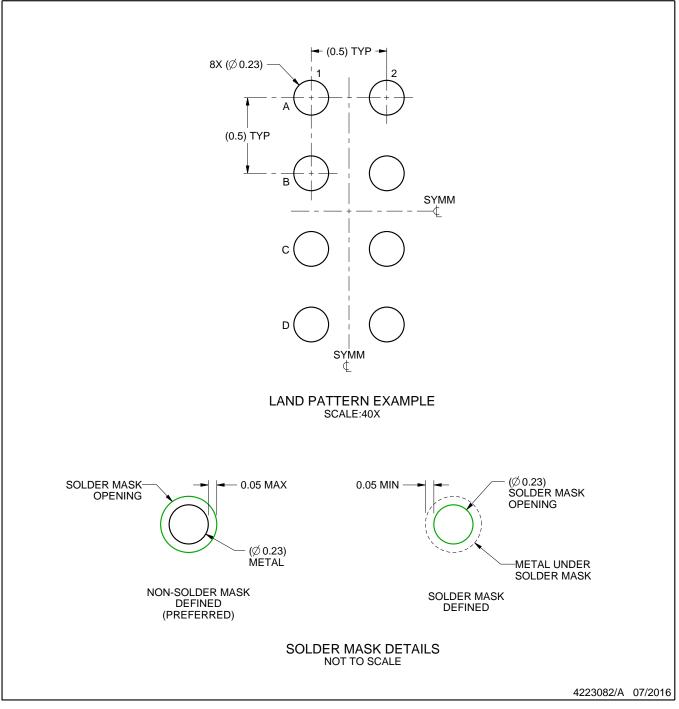
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.

YZP0008

EXAMPLE BOARD LAYOUT

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

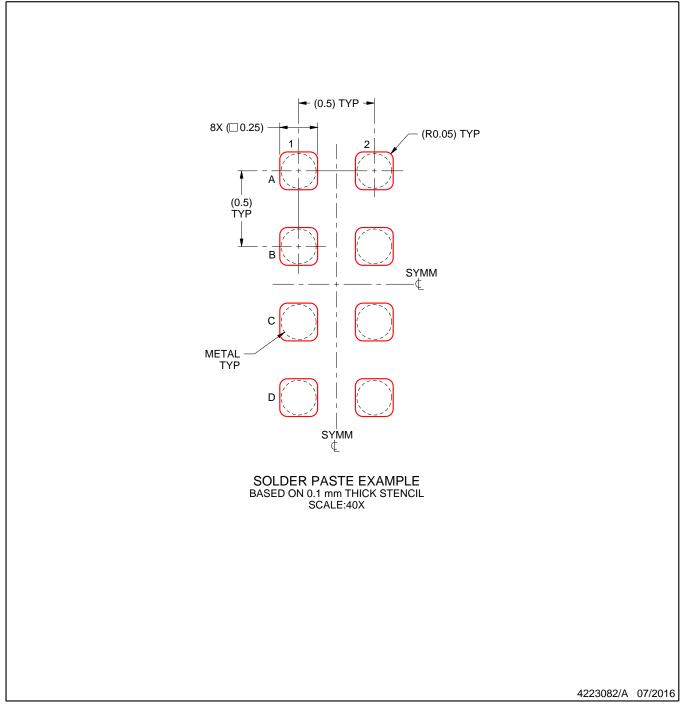
3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

YZP0008

EXAMPLE STENCIL DESIGN

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

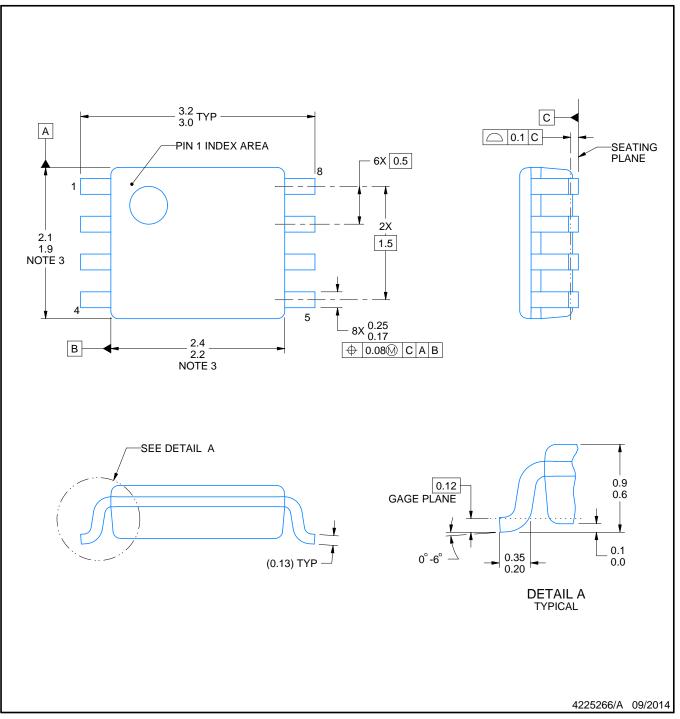
DCU0008A



PACKAGE OUTLINE

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



NOTES:

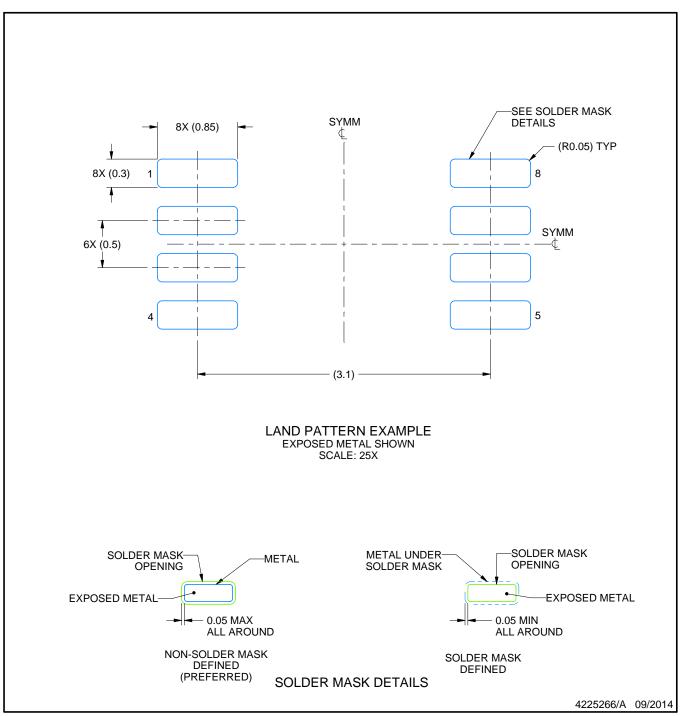
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side. 4. Reference JEDEC registration MO-187 variation CA.

DCU0008A

EXAMPLE BOARD LAYOUT

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

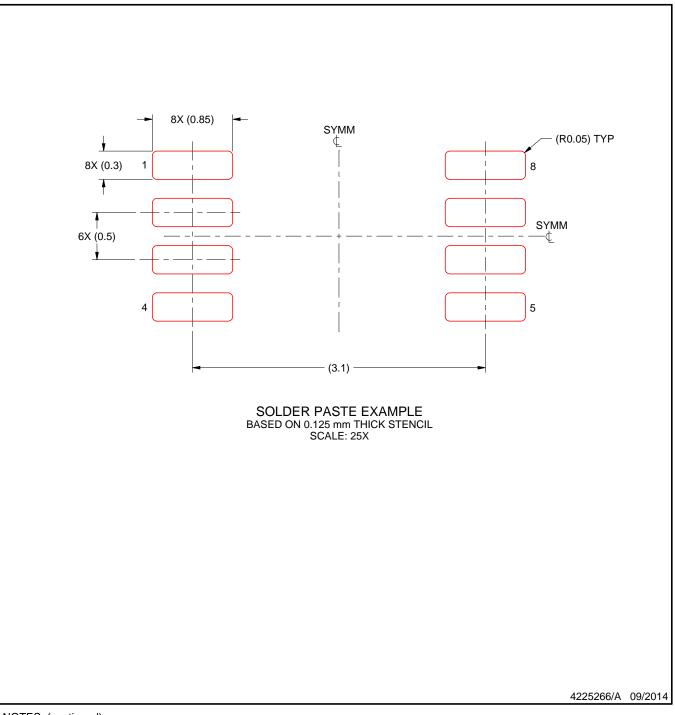
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

DCU0008A

EXAMPLE STENCIL DESIGN

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

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